

GaAs monolithic microwave power splitter

8~12GHz

**key indicator**

- Frequency range: 8~12GHz
- Insertion loss: ≤0.8dB@12GHz
- Good input/output standing wave ratio: ≤1.3:1
- Chip size: 1.0mm×1.25mm×0.1mm

**typical application**

- Radar and electronic countermeasures
- RF/Microwave Circuit
- Military and aerospace
- Test measurement
- Instrumentation

**Product Introduction**

AY1360 is a 0° ultra-wideband power divider chip, the working frequency covers 8~12GHz, the insertion loss is less than 0.8dB, The standing wave ratio is less than 1.3:1.

The chip adopts an on-chip metallization process to ensure good grounding, and is suitable for eutectic sintering or conductive adhesive bonding processes.

**Electrical performance (T<sub>A</sub>=25 °C, Z<sub>0</sub>=50Ω)**

parameter name	symbol	Test Conditions	Parameter value			unit
			MIN	TYP	MAX	
Frequency Range	f	Z <sub>in</sub> =Z <sub>out</sub> =50Ω T <sub>A</sub> =+25°C	8	—	12	GHz
Insertion loss	IL		—	—	-0.9	dB
Insertion loss balance	IP		—	±0.05	—	dB
Input standing wave ratio	VSWR		—	—	1.3	:1
Output standing wave ratio			—	—	1.3	:1
Isolation	ISO		-23	—	—	dB

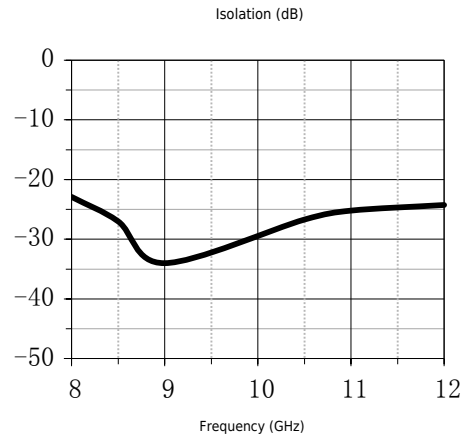
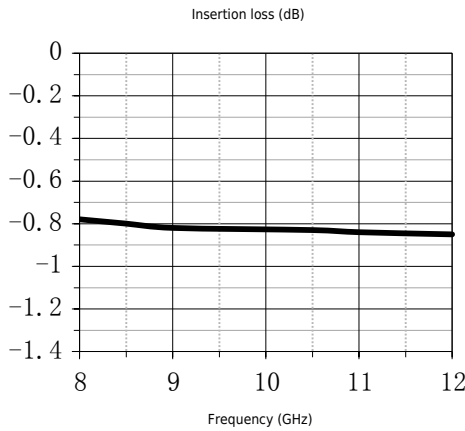
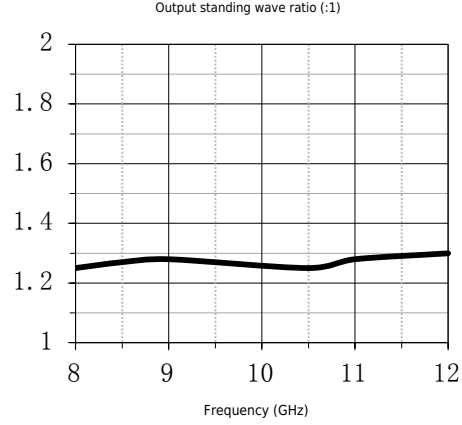
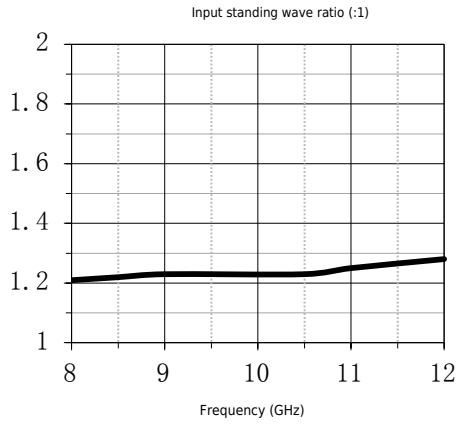
**Absolute maximum ratings**

Maximum input RF power	+22dBm	Operating temperature	-55 °C ~ + 85 °C
Channel temperature	150 °C	Storage temperature	-65 °C ~ + 150 °C

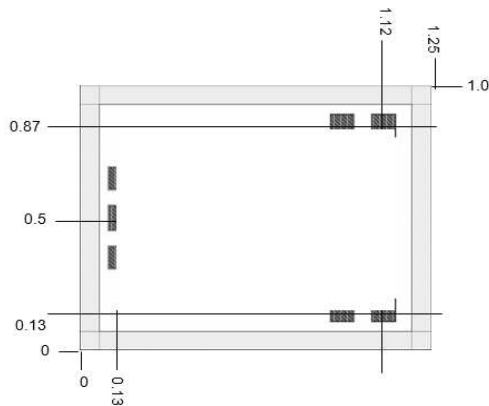
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Typical test curve



Shape and port size (mm)



Precautions

Gallium arsenide MMIC devices are susceptible to electrostatic discharge damage. Precautions should be taken during transportation, assembly and testing.